

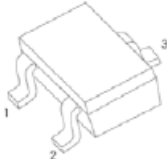
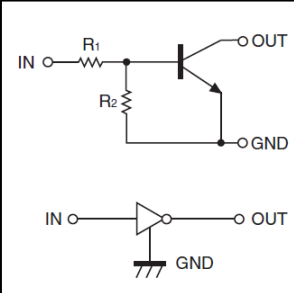
## Digital Transistors (Built-in Resistors)

### DTC115EE DIGITAL TRANSISTOR (NPN)

#### FEATURES

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors(see equivalent circuit)
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input.They also have the advantage of almost completely eliminating parasitic effects
- Only the on/off conditions need to be set for operation, making device design easy

#### PIN CONNENCTIONS, MARKING and EQUIVALENT CIRCUIT

<p><b>DTC115EE</b></p>  <p><b>MARKING: 29</b></p>	<p><b>SOT-523</b></p> <p>1. IN 2. GND 3. OUT</p>	<p><b>Equivalent Circuit</b></p> 
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#### MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>CC</sub>	Supply Voltage	50	V
V <sub>IN</sub>	Input Voltage	-10~+40	V
I <sub>O</sub>	Output Current	100	mA
P <sub>D</sub>	Power Dissipation	150	mW
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

#### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input voltage	V <sub>I(off)</sub>	V <sub>CC</sub> =5V, I <sub>O</sub> =100μA	0.5			V
	V <sub>I(on)</sub>	V <sub>O</sub> =0.3V, I <sub>O</sub> =1mA			3	V
Output voltage	V <sub>O(on)</sub>	I <sub>O</sub> /I <sub>I</sub> =5mA/0.25mA		0.1	0.3	V
Input current	I <sub>I</sub>	V <sub>I</sub> =5V			0.15	mA
Output current	I <sub>O(off)</sub>	V <sub>CC</sub> =50V, V <sub>I</sub> =0V			0.5	μA
DC current gain	G <sub>I</sub>	V <sub>O</sub> =5V, I <sub>O</sub> =5mA	82			
Input resistance	R <sub>1</sub>		70	100	130	kΩ
Resistance ratio	R <sub>2</sub> /R <sub>1</sub>		0.8	1	1.2	
Transition frequency	f <sub>T</sub>	V <sub>O</sub> =10V, I <sub>O</sub> =5mA, f=100MHz		250		MHz